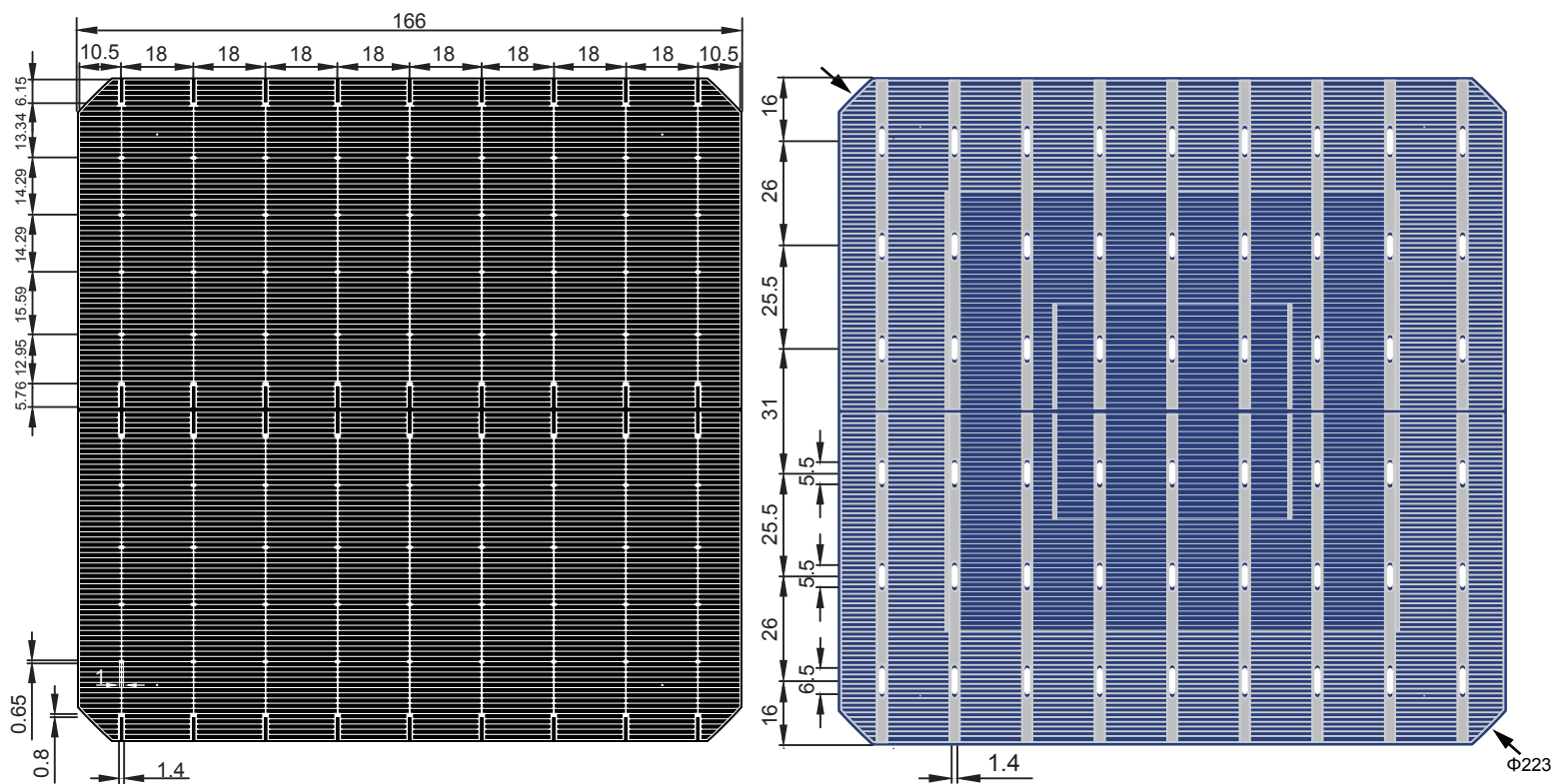




Mono-crystalline Silicon 6" PERC Bifacial Solar Cell

B7F9H



Physical Characteristics

Cell type	Mono-crystalline Silicon PERC Bifacial Solar Cell
Dimension	166 mm X 166 mm $\pm$ 0.25 mm 223 mm $\pm$ 0.25 mm (Diagonal length)
Cell thickness	170 μ m $\pm$ 30 μ m
Front side (—)	Silicon nitride anti-reflective coating and 128 fingers Nine 0.1 $\pm$ 0.03 mm wide bus bars with distance 18.0 mm
Back side (+)	Silicon nitride anti-reflection coating Nine 1.4 $\pm$ 0.1 mm discontinuous soldering pads

B7F9H

General Characteristics

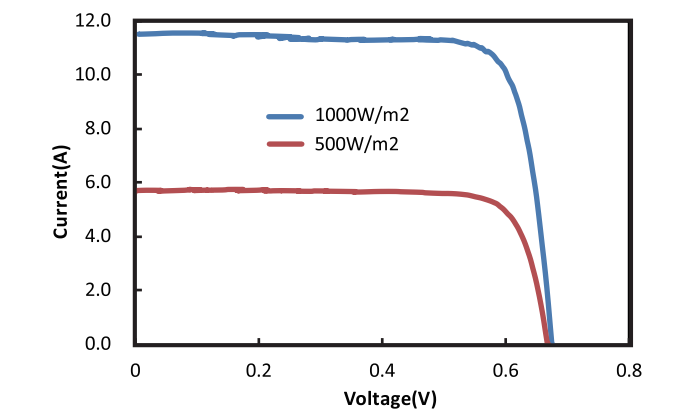
Eff(%)	Pmpp(Pmax)	Voc	Isc	Vmpp(Vmp)	Impp(Imp)
22.2	6.086	0.677	11.534	0.560	10.874
22.3	6.114	0.678	11.537	0.561	10.892
22.4	6.141	0.679	11.549	0.563	10.908
22.5	6.168	0.680	11.558	0.565	10.916
22.6	6.196	0.681	11.564	0.567	10.926
22.7	6.223	0.682	11.572	0.569	10.938
22.8	6.251	0.683	11.577	0.571	10.951
22.9	6.278	0.684	11.579	0.572	10.968
23.0	6.305	0.685	11.581	0.574	10.980
23.1	6.333	0.685	11.585	0.575	11.009
23.2	6.360	0.686	11.591	0.576	11.040
23.3	6.388	0.686	11.597	0.578	11.062

- Under standard test condition : 1000W / m2 , AM 1.5 , 25°C ● Illustration : 22.8% → actual range 22.80%~22.89%
- Specification and data are for reference only and may change without prior notice.

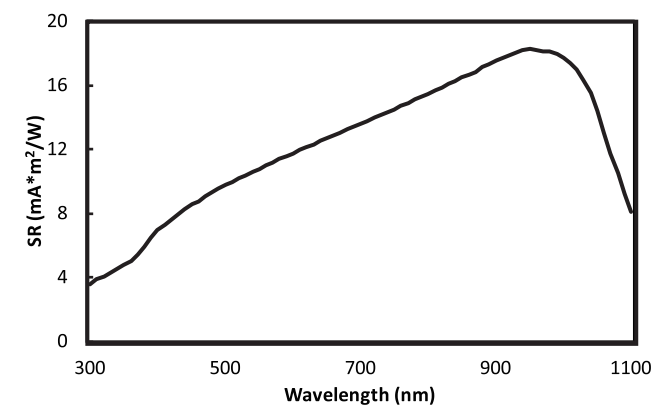
Temperature Coefficient

Voc	Isc	FF	Power
-0.2662%/K	0.0624%/K	-0.1071%/K	-0.3086%/K

Typical I-V Curve



Spectral Response



Electrical Properties

Parameter	Grade A
Cell efficiency / P _{mp}	Measured cell efficiency (or P _{mp}) according to above mentioned bin criteria (AM 1.5, 1000 W/m ² , 25 °C)
Shunt resistivity	> 30 Ohm
Reverse dark current	I _{rev 2} < 1.0 A at -12V and 25°C